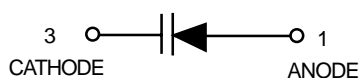


# Silicon Pin Diode

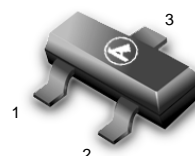
This device is designed primarily for VHF band switching applications but is also suitable for use in general-purpose switching circuits. Supplied in a surface Mount package.

- Rugged Pin Structure Coupled with Wirebond Construction for Optimum Reliability
- Low Capacitance—0.7pF Typ at VR=20Vdc
- Very Low Series Resistance at 100MHz—0.34Ohms(Typ)@IF=10mAdc



**MMBV3401LT1**

**SILICON PIN SWITCHING DIODE**



**CASE 318-08, STYLE 6  
SOT- 23 (TO-236AB)**

### MAXIMUM RATINGS(EACH DIODE)

Rating	Symbol	Value	Unit
Reverse Voltage	$V_R$	20	Vdc
Forward power Dissipation @ $T_A = 25^\circ\text{C}$	$P_D$	200	mW
Derate above 25°C		2.0	mW/°C
Junction Temperature	$T_J$	+125	°C
Storage Temperature Range	$T_{slg}$	-55 to +150	°C

### DEVICE MARKING

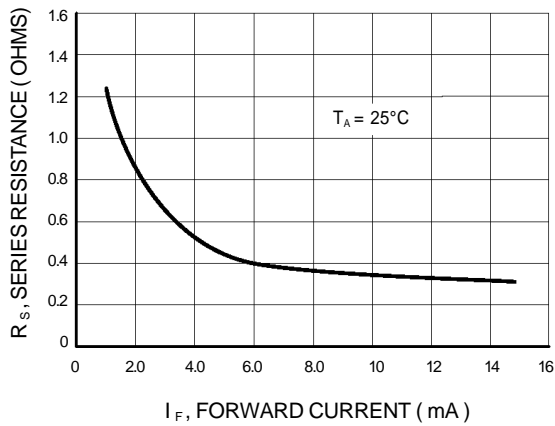
MMBV3401LT1=4D

### ELECTRICAL CHARACTERISTICS( $T_A=25^\circ\text{C}$ unless otherwise noted)

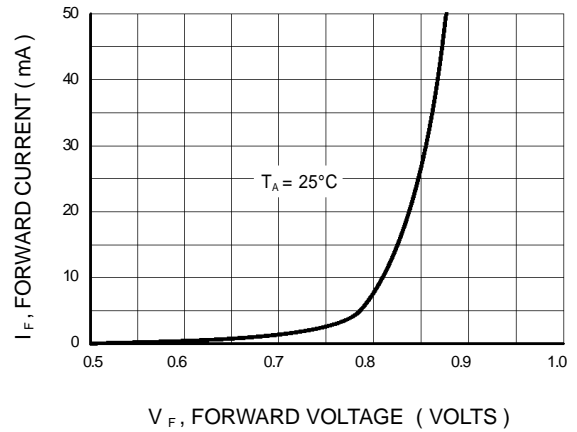
Characteristic	Symbol	Min	Typ	Max	Unit
Reverse Breakdown Voltage ( $I_R=10\mu\text{Adc}$ )	$V_{(BR)R}$	35	—	—	Vdc
Diode Capacitance ( $V_R=20\text{ Vdc}$ )	$C_T$	—	—	1.0	pF
Series Resistance(figure5) ( $I_F=10\text{mAdc}, f=100\text{MHz}$ )	$R_S$	—	—	0.7	$\Omega$
Reverse Voltage Leakage Current ( $V_R=15\text{Vdc}$ )	$I_R$	—	—	0.1	$\mu\text{Adc}$

**MMBV3401LT1**

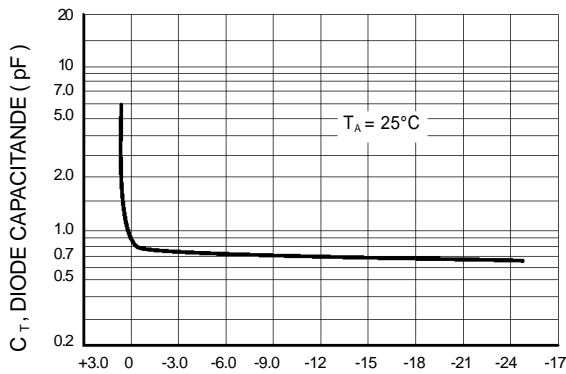
**TYPICAL CHARACTERISTICS**



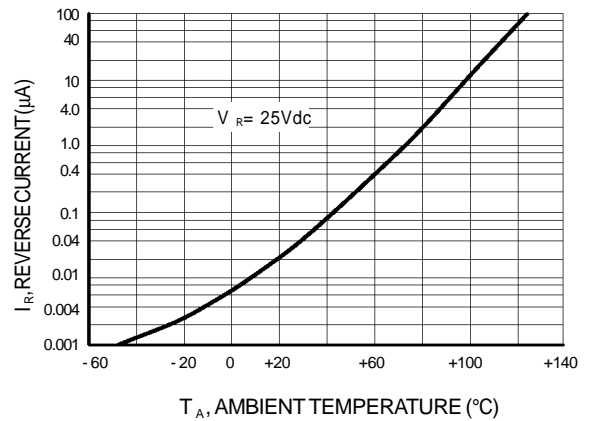
**Figure 1. Series Resistance**



**Figure 2. Forward Voltage**



**Figure 3. Diode Capacitance**



**Figure 4. Leakage Current**